IN THE SPECIFICATION:

On page 6, please amend the second full paragraph continuing to page 7 as follows:

~~The present inventors have found that, by~~ By setting the thickness of the protective insulating film 8 at 100 nm or less instead of approximately 200 nm in the process for fabricating the conventional bottom-gate TFT, and by injecting the dopant through the protective insulating film 8 when the LDD region 9, or the source-drain region 10 is formed subsequently, it is possible to eliminate the etching step of the protective insulating film 8 and also an insufficient breakdown voltage of the gate insulating film 6 can be overcome. Moreover, it has also been found that the structure of such a TFT or the method for fabricating the same can be employed for liquid crystal display devices and organic EL devices driven by TFTs.

C1

On page 10, please amend the first paragraph as follows:

FIGs. ~~3G to 3J~~ 3A to 3D are schematic sectional views showing the steps for fabricating the liquid crystal display device subsequent to the steps shown in FIGs. 2A to 2F;

C2

On page 10, please amend the eighth paragraph continuing to page 11 as follows:

FIG. 1 is a schematic sectional view of a liquid crystal display device using a bottom-gate thin-film transistor in an embodiment of the present invention, and FIGs. 2A to 2F and FIGs. ~~3G to 3J~~ 3A to 3D are schematic sectional views showing the steps for fabricating the liquid crystal display device shown in FIG. 1.

C3

On page 15, please amend the first paragraph was amended as follows:

Next, an interlayer insulating film 13 is formed, a source electrode 17 and a drain electrode 18 are formed, a transparent electrode 20 is formed, and an alignment layer 21 is formed on the transparent electrode 20 in a manner similar to that in the conventional method. That is, in order to form the interlayer insulating film 13, a silicon nitride film 14 (50 to 500 nm) and a silicon oxide film 15 (50 to 500 nm) are continuously deposited, as shown in FIG [[3G]] 3A. Next, contact holes 16 are made by etching the interlayer insulating film 13 and the gate insulating film 6, as shown in FIG. [[3H]] 3B, and a metal, such as Al, is embedded in the contact holes 16 to form the source electrode 17 and the drain electrode 18, as shown in FIG. [[3I]] 3C. The planarizing layer 19 formed of an organic planarizing film composed of an organic acrylic resin, a silicon nitride planarizing film, or the like is formed in the region excluding a section for forming a contact with the transparent electrode of the liquid crystal display panel and a pad-forming section. The transparent electrode 20 composed of ITO or the like is then formed so as to cover the pixel section, and the alignment layer 21 is formed on the transparent electrode 20. Thus, a TFT substrate 201A for a liquid crystal display device having the TFT 100A of the present invention as the active element is obtained, as shown in FIG. [[3J]] 3D.